

Ionizing Radiation Detector Circuits and their Operations



Hristo Sabev¹ and Tsanko Karadzhov²

¹Hristo Sabev is with the Faculty of Electrical Engineering and Electronics at Technical University of Gabrovo, 4 H. Dimitar, Gabrovo 5300, Bulgaria

²Tsanko Karadzhov is with the Faculty of Mechanical and Precision Engineering at Technical University of Gabrovo, 4 H. Dimitar, Gabrovo 5300, Bulgaria

ABSTRACT: *The functioning of the ionizing radiation detector circuits and their operations are tested using simulations in the current work. We have verified the semiconductor optoelectronic detectors of ionizing radiation. Based on the outcome we proposed circuits for temperature compensation in the optoelectronic detectors performance with low energy levels. This environment has the ionizing particles in fast and slow changes. We have applied the trial results of the opto-electronic detectors.*

Keywords: Ionizing Radiations, PIN Photodiodes, PSPICE Simulations

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1. Introduction

Standards for optoelectronic detectors of ionizing radiations are given in [1, 2, 3]. The optoelectronic detectors of ionizing radiations, including PIN photodiodes, are viewed in [4, 5, 6, 7, 8, 10, 11]. The operation of three circuits of ionizing radiation detectors, realized by means of PIN photodiodes, are simulated. They are considered in [9].

2. Optoelectronic Circuits of Detectors

Figure 1 shows a circuit where the PIN photodiode is connected to an AC current circuit. The circuit is used for registering ionizing radiations. The photodiode operates under inverse voltage in photodiode mode. The amplifier DA1 has a high input resistance. A silicon PIN photodiode SFH 520 of large area is used [11].

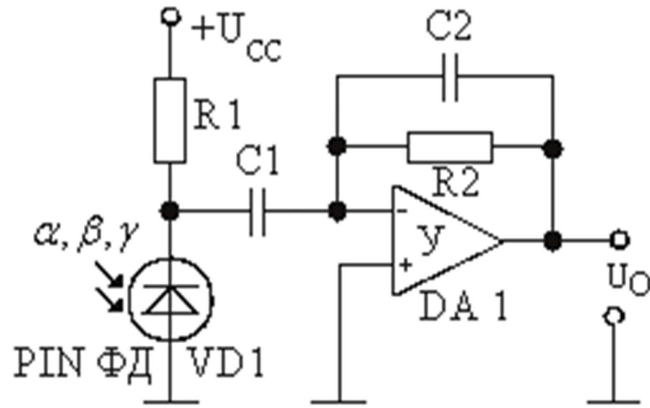


Figure 1. Circuit where the PIN photodiode is connected

Within the next circuits an operating photodiode (VD1) and a compensating photodiode (VD2) are used.

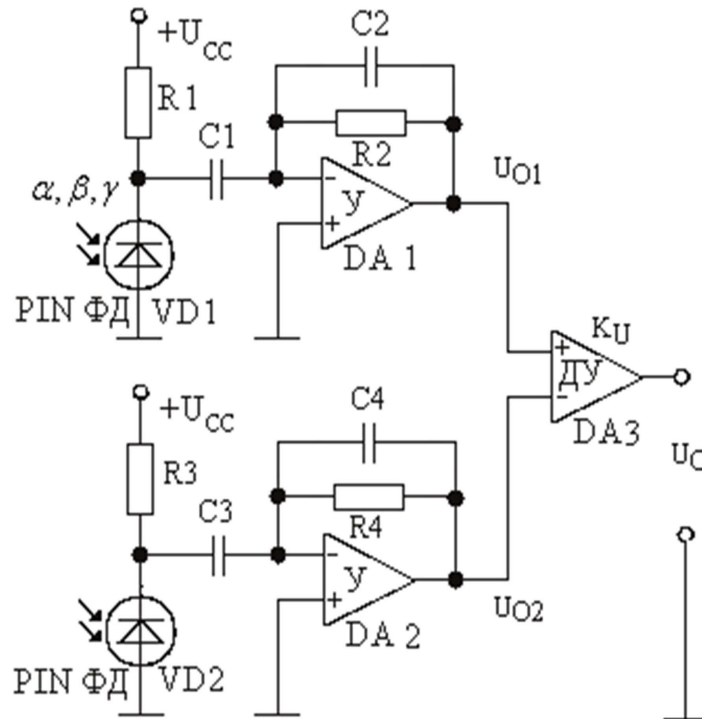


Figure 2. A detector circuit with compensation of fast temperature changes

The output circuit voltage is:

$$U_O = K_U \cdot I_{ph1} \cdot R_2 \quad (1)$$

$$U_O = K_U \cdot (U_{O1} - U_{O2}) = K_U \cdot [(I_{ph1} + I_{D1}) \cdot R_2 - I_{D2} \cdot R_2] = K_U \cdot I_{ph1} \cdot R_2 \quad (2)$$

When the photodiodes are identical, the two dark currents are equal $I_{D1} = I_{D2}$

where K_U - coefficient of amplification according to the voltage of the differential amplifier DA3, I_{ph1} - photocurrent of the PIN photodiode 1, I_{D1} , I_{D2} - dark currents of the PIN photodiodes 1 and 2. The following conditions must be satisfied:

$$R1 = R3; R2 = R4; C1 = C3; C2 = C4 \quad I_{ph2} = 0 \quad (3)$$

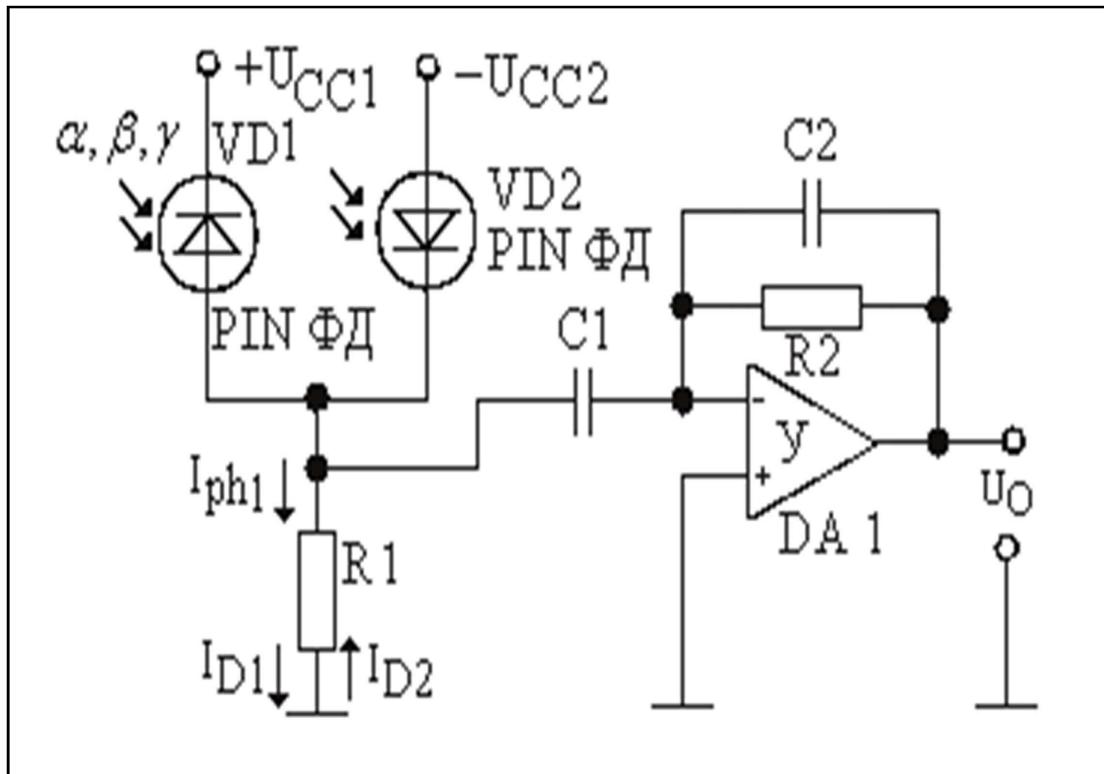


Figure 3. A detector circuit with compensation of slow temperature changes

The supply voltages of the circuit are equal $U_{CC1} = U_{CC2}$

The voltage on the resistor R1 is:

$$U_{R1} = [I_{ph1} + (I_{D1} - I_{D2})] \cdot R_1 = I_{ph1} \cdot R_1$$

$$I_{D1} = I_{D2}; I_{ph2} = 0$$

$$I_{D1} = I_{D2}; I_{ph2} = 0 \quad (4)$$

For the circuits in figure 2 and figure 3 differential detectors or coordinate (position)-sensitive detectors (PSD) should be used.

For an operation in a wide temperature range the photodiodes of ORTEC company should be used [10].

ORTEC produces photon detectors made of high purity germanium (G?), of a P or N type with a cryostat.

The circuits in figure 1, 2 and 3 possess a common basic circuit shown in figure 4.

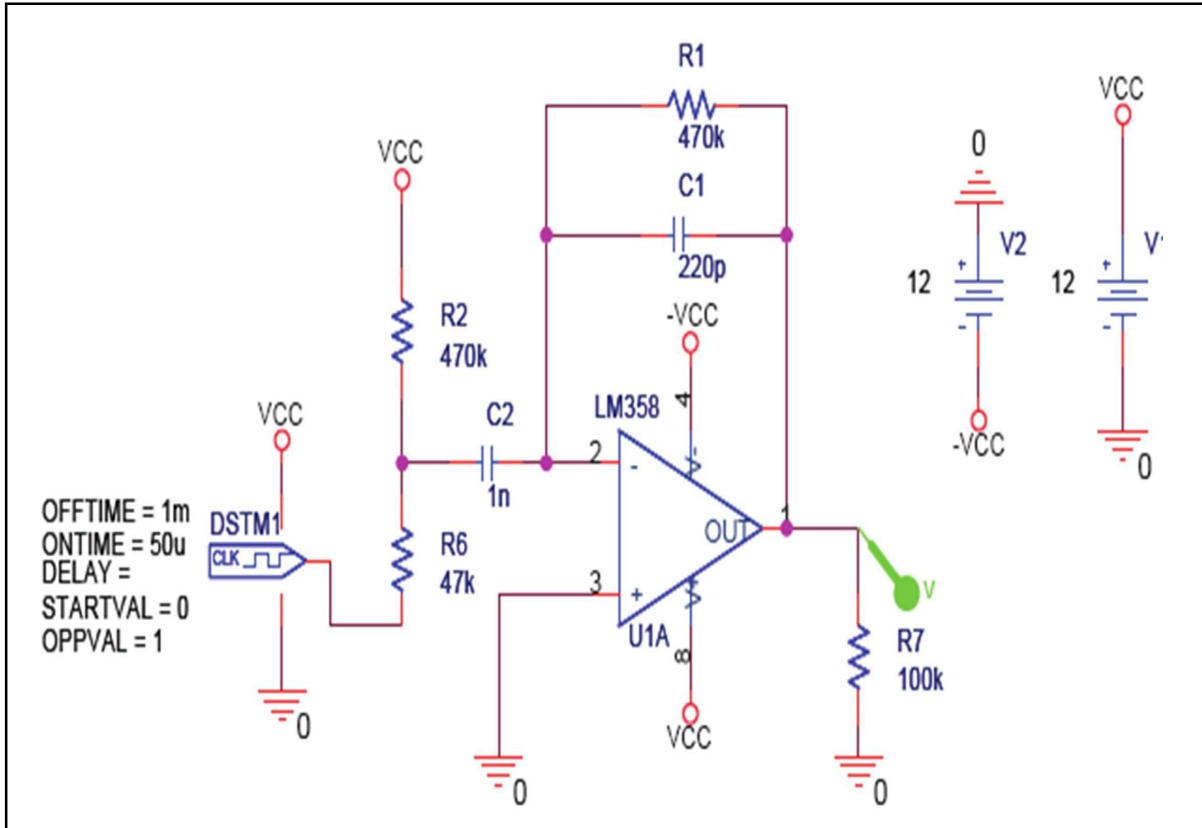


Figure 4. Basic circuit for PSPICE simulations of optoelectronic detectors

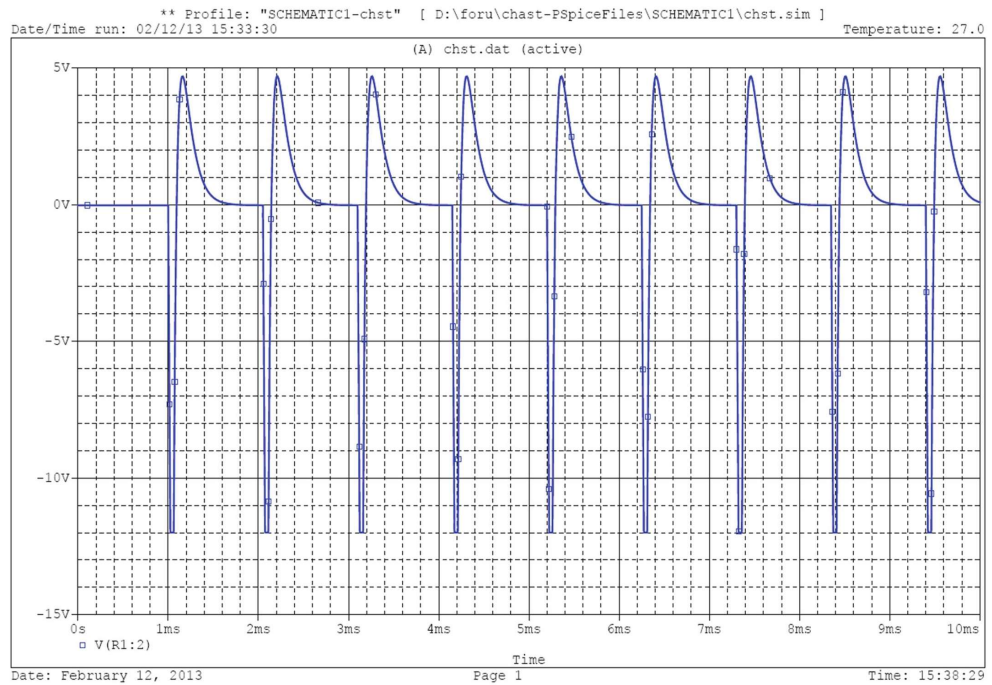


Figure 4a. Output voltage of the circuit in figure 4

3. Conclusion

Circuits of optoelectronic detectors of ionizing radiation, implemented by means of PIN photodiodes, are simulated. The results from the simulations are compared with those obtained from the calculations and measurements done.

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